

N-channel TrenchMOS logic level FET Rev. 02 — 27 January 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- 1.3 Applications
 - 12 V, 24 V and 42 V loads
 - Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Suitable for logic level gate drive
sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

Parameter	Conditions	Min	Тур	Мах	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	75	V
drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	45	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	114	W
aracteristics					
drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C	-	-	29	mΩ
	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	20.9	24.6	mΩ
	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	22.1	26	mΩ
ne ruggedness					
non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 49 \text{ A}; V_{sup} \leq 75 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	120	mJ
	drain-source voltage drain current total power dissipation aracteristics drain-source on-state resistance non-repetitive drain-source	$\label{eq:generalized_set} \begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{cccc} \text{drain-source voltage} & T_j \geq 25 \ ^\circ\text{C}; \ T_j \leq 175 \ ^\circ\text{C} & - & - & 75 \\ \text{drain current} & V_{\text{GS}} = 5 \ ^\circ\text{Y}; \ T_{\text{mb}} = 25 \ ^\circ\text{C}; & - & - & 45 \\ \text{see Figure 1; see Figure 3} & - & - & 45 \\ \text{total power dissipation} & T_{\text{mb}} = 25 \ ^\circ\text{C}; \text{see Figure 2} & - & - & 114 \\ \hline \textbf{aracteristics} & & & & \\ \text{drain-source on-state} & V_{\text{GS}} = 4.5 \ ^\circ\text{Y}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C} & - & - & 29 \\ \hline V_{\text{GS}} = 10 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C} & - & 20.9 \\ \hline V_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \text{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \textbf{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \textbf{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{C}; & - & 22.1 \ ^\circ\text{C}; \\ \text{see Figure 13; see Figure 12} & - & - & 120 \\ \hline \textbf{mon-repetitive} & I_D = 49 \ ^\circ\text{A}; \ V_{\text{Sup}} \leq 75 \ ^\circ\text{V}; & - & - & 120 \\ \hline \textbf{R}_{\text{GS}} = 50 \ ^\circ\text{Q}; \ V_{\text{GS}} = 5 \ ^\circ\text{V}; \end{array}$

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9226-75A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

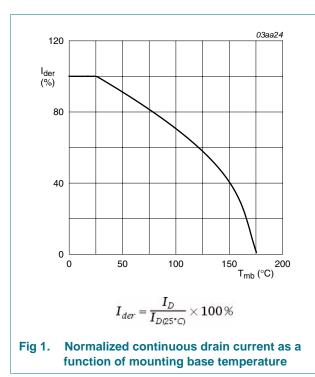
4. Limiting values

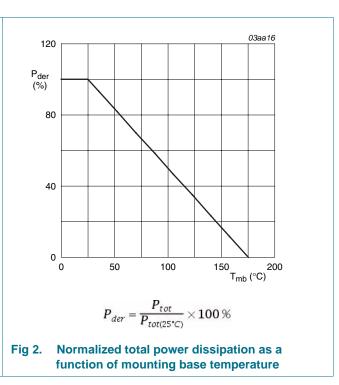
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Mox	l lni+
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
V _{GS}	gate-source voltage		-10	10	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	45	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	32	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}; $ see <u>Figure 3</u>	1 -	182	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	114	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 µs	-15	15	V
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	45	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	182	А
Avalanche I	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 49 \text{ A}; V_{sup} \le 75 \text{ V}; \text{ R}_{GS} = 50 \Omega;$ $V_{GS} = 5 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}$	-	120	mJ

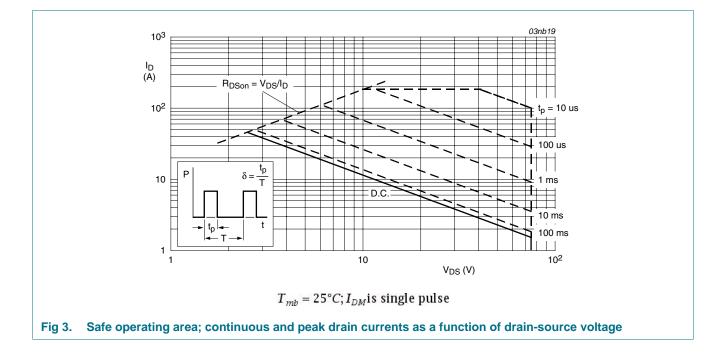
[1] Peak drain current is limited by chip, not package.





BUK9226-75A

N-channel TrenchMOS logic level FET



5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	71.4	-	K/W

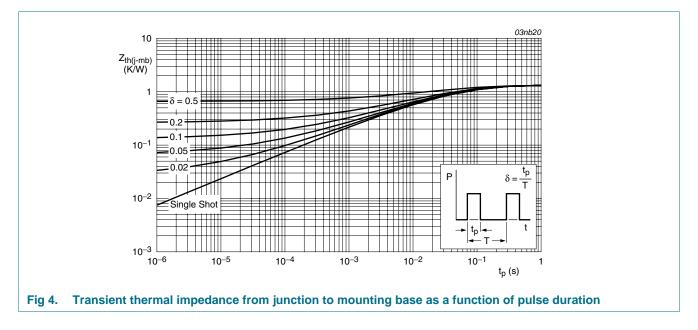


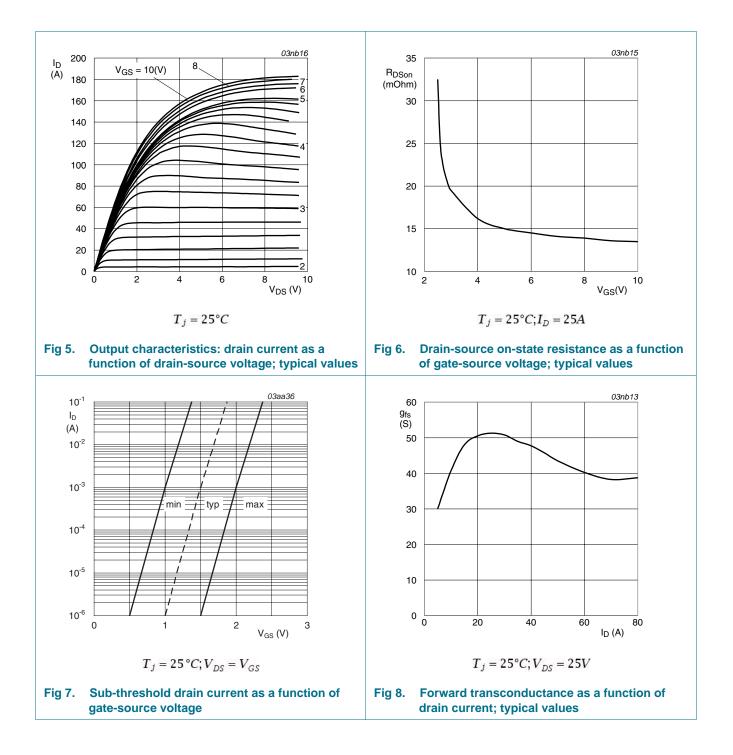
Table 5. Thermal characteristics

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	75	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	70	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	54.6	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	29	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	20.9	24.6	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13; see Figure 12	-	22.1	26	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	2340	3120	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	319	383	pF
C _{rss}	reverse transfer capacitance		-	215	295	pF
t _{d(on)}	turn-on delay time	$V_{DS}=30 \text{ V}; \text{ R}_{L}=1.2 \Omega; V_{GS}=5 \text{ V}; \label{eq:VDS}$	-	24	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	141	-	ns
t _{d(off)}	turn-off delay time		-	142	-	ns
t _f	fall time		-	108	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die ; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	measured from source lead from package to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$ I_S = 20 \text{ A}; \ dI_S/dt = 100 \text{ A}/\mu\text{s}; \\ V_{GS} = -10 \text{ V}; \ V_{DS} = 30 \text{ V}; \ T_j = 25 \ ^\circ\text{C} $	-	49	-	ns
Q _r	recovered charge	I _S = 20 A; dI _S /dt = -100 A/µs; V _{GS} = -10 V; V _{DS} = 30 V; T _i = 25 °C	-	115	-	nC

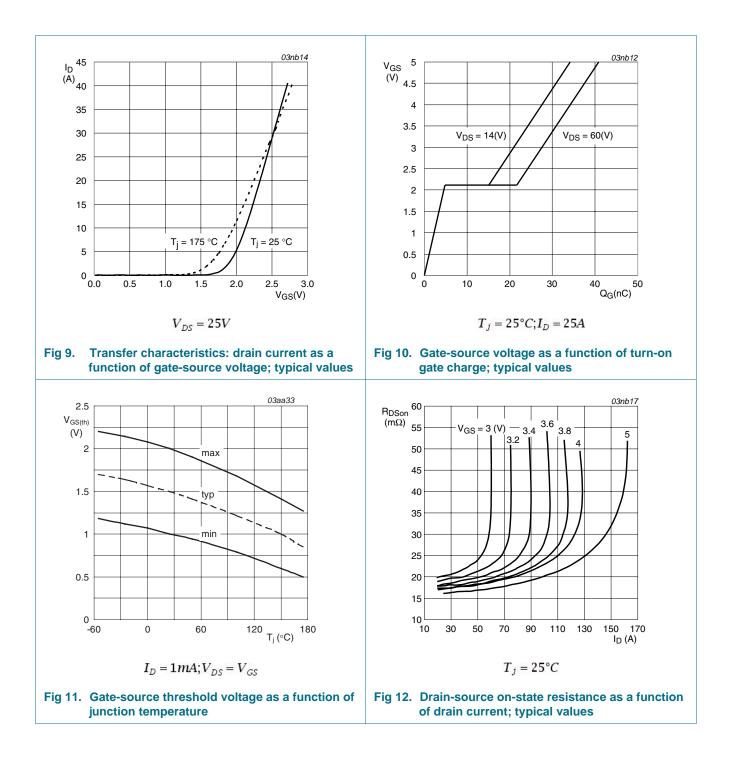
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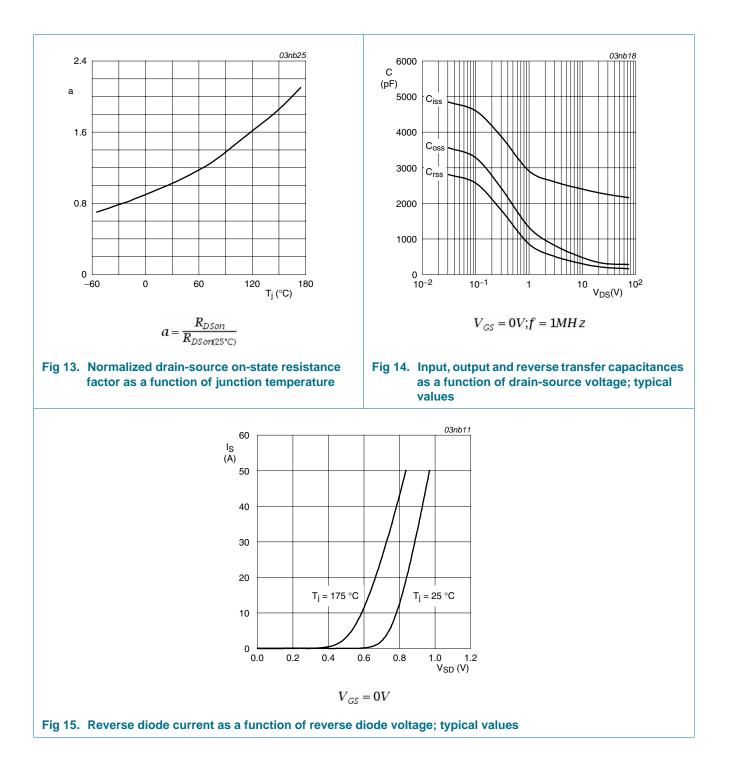
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7. Package outline

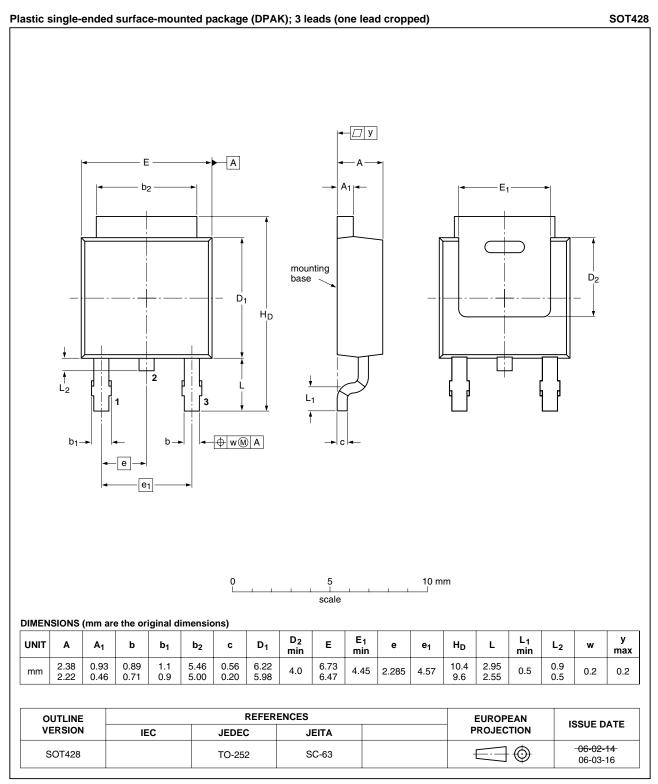


Fig 16. Package outline SOT428 (DPAK)

BUK9226-75A Product data sheet

8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9226-75A v.2	20110127	Product data sheet	-	BUK9226_75A v.1
Modifications:	 The format of of NXP Semic 	this data sheet has been rec onductors.	designed to comply with	n the new identity guidelines
	 Legal texts hat 	ve been adapted to the new	company name where	appropriate.
BUK9226_75A v.1	20001010	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS logic level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status12
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks
10	Contact information13

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